

a semiconductor light-emitting chip electrically connected to said pair of electrodes;

a mold encapsulating said semiconductor light-emitting chip, said mold encapsulating said inner portion of at least one of said pair of electrodes, said outer portion of at least one of said pair of electrodes extending substantially laterally beyond said mold; and

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a step formed in said inner portion of at least one of said pair of electrodes at an inside of said mold, said step having a height increasing from an outer side to an inner side of said mold.

2. (Amended) A chip-type semiconductor light-emitting device according to claim 1, wherein said electrode includes a Cu layer, said step being formed by changing a thickness of said Cu layer.

IN THE ABSTRACT:

Please replace the Abstract with the following:

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A chip-type semiconductor light-emitting device includes a semiconductor light-emitting chip connected to a pair of electrodes formed on a substrate. The semiconductor light-emitting chip is molded, together with respective parts of the electrodes, by resin. The electrode has a layered structure having a Cu layer, an Ni layer and an Au layer in that order from the lowermost layer, to have a step formed inside the mold by changing the wall thickness of the Cu layer.

REMARKS

The non-final Office Action mailed February 7, 2002 and the references cited therein have been carefully considered. Claim 1 has been amended to further clarify that the chip-type semiconductor light-emitting device does not include a substrate and that a step is formed inside a mold in an inner portion of an electrode. Claim 2 has been amended to further clarify that the step is formed by changing a thickness of a copper (Cu) layer.

No new matter has been added to Claims 1 and 2, as amended. Support for this Amendment is found generally within the specification, claims, and drawings, as originally